TOSHIBA Photocoupler IRED & Photo-Triac

TLP363JF

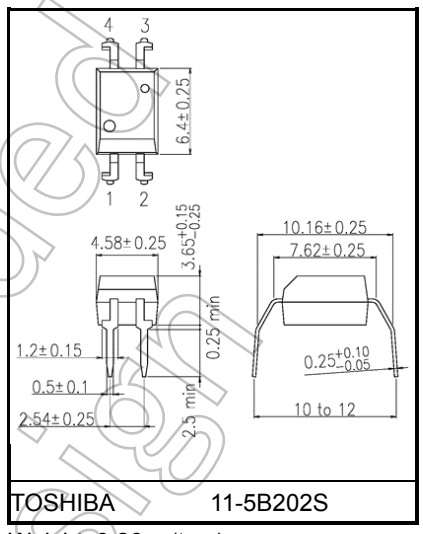
Triac Drivers

Programmable Controllers

AC-Output Modules

Solid State Relays

Unit: mm



TOSHIBA 11-5B202S

Weight: 0.26 g (typ.)

TOSHIBA TLP363JF consists of a zero-voltage-crossing turn-on photo-triac optically coupled to an infrared emitting diode in a four-lead plastic DIP package. This product has a greater capacity to withstand external noise than the TLP361JF.

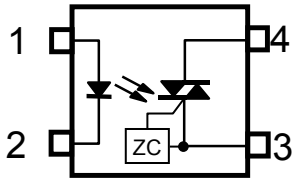
- Peak off-state voltage: 600 V (min)
- Trigger LED current: 10 mA (max)
- On-state current: 100 mA (max)
- Isolation voltage: 5000 Vrms (min)
- Zero crossing function
- UL-recognized: UL 1577, File No.E67349
- cUL-recognized: CSA Component Acceptance Service No.5A
  File No.E67349
- CQC approved: GB4943.1, GB8898 Japan Factory
- VDE-approved: EN 60747-5-5 , EN 62368-1 (Note 1)

Note 1: When a VDE approved type is needed, please designate the **Option(D4)**.

•Construction mechanical rating

Creepage distance	8.0 mm (min)
Clearance	8.0 mm (min)
Insulation thickness	0.4 mm (min)

Pin Configuration (top view)



1: Anode
2: Cathode
3: Triac T1
4: Triac T2

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Start of commercial production
2004-01

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Absolute Maximum Ratings (Ta = 25°C)

	Characteristic		Symbol	Rating	Unit
LED	Forward current		I_F	50	mA
	Forward current derating (Ta ≥ 53°C)		ΔI_F /°C	-0.7	mA /°C
	Peak forward current (100 μs pulse, 100 pps)		I_{FP}	1	A
	Reverse voltage		V_R	5	V
	Diode power dissipation		P_D	72	mW
	Diode power dissipation derating (Ta ≥ 53°C)		ΔP_D /°C	-1.0	mW/°C
	Junction temperature		T_j	125	°C
Detector	Off-state output terminal voltage		V_{DRM}	600	V
	On-state RMS current	Ta = 25°C	$I_{T(RMS)}$	100	mA
		Ta = 70°C		50	
	On-state current derating (Ta ≥ 25°C)		ΔI_T/°C	-1.1	mA /°C
	Peak on-state current (100 μs pulse, 120 pps)		I_{TP}	2	A
	Peak non-repetitive surge current (Pw =10 ms)		I_{TSM}	1.2	A
	Output power dissipation		Po	300	mW
	Output power dissipation derating (Ta ≥ 25°C)		ΔP_O / °C	-3.0	mW / °C
	Junction temperature		T_j	115	°C
Storage temperature range			T_{stg}	-55 to 125	°C
Operating temperature range			T_{opr}	-40 to 100	°C
Lead soldering temperature (10 s)			T_{sol}	260	°C
Isolation voltage (AC, 60 s, R.H. ≤ 60 %)		(Note 1)	BV_S	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pins 1 and 2 are shorted together and pins 3 and 4 are shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min	Typ.	Max	Unit
Supply voltage	V_{AC}	—	—	240	V_{ac}
Forward current	I_F	15	20	25	mA
Peak on-state current	I_{TP}	—	—	1	A
Operating temperature	T_{opr}	-25	—	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

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Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
LED	Forward Voltage	V_F	I_F = 10 mA	1.0	1.15	1.3	V
LED	Reverse Current	I_R	V_R = 5 V	—	—	10	μA
LED	Capacitance	C_T	V = 0 V, f = 1 MHz	—	30	—	pF
Detector	Peak off-state current	I_{DRM}	V_{DRM} = 600 V	—	10	1000	nA
Detector	Peak on-state voltage	V_{TM}	I_{TM} = 100 mA	—	1.7	3.0	V
Detector	Holding current	I_H	—	—	0.6	—	mA
Detector	Critical rate of rise of off-state voltage	dv/dt	Vin = 240 Vrms, Ta = 85 °C (Note 2)	200	500	—	V/μs
Detector	Critical rate of rise of commutating voltage	dv/dt(c)	Vin = 60 Vrms, I_T = 15 mA (Note 2)	—	0.2	—	V/μs

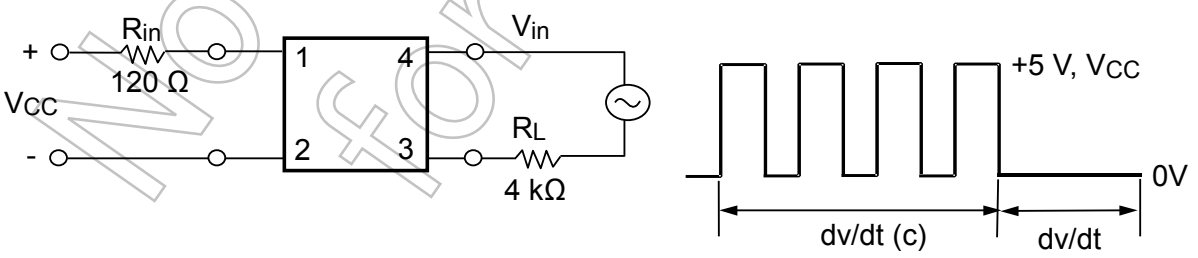
Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Trigger LED current	I_{FT}	V_T = 3 V	—	—	10	mA
Inhibit voltage	V_{IH}	I_F = Rated I_{FT}	—	—	20	V
Leakage in inhibited state	I_{IH}	I_F = Rated I_{FT} V_T = Rated V_{DRM}	—	200	600	μA
Turn-on time	t_{ON}	V_D =3 → 1.5 V , R_L = 20 Ω I_F = Rated I_{FT}X1.5	—	30	100	μs
Impulse noise durability	V_N	t_N=1μs, Snuber condition 100 Ω +0.033 μF (Note.3)	—	2000	—	V

Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Capacitance (input to output)	C_S	V_S = 0 V, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R_S	V_S = 500 V, R.H.≤ 60 %	1×10^{12}	10^{14}	—	Ω
Isolation voltage	BV_S	AC, 60 s	5000	—	—	Vrms

Note 2: dv/dt test circuit



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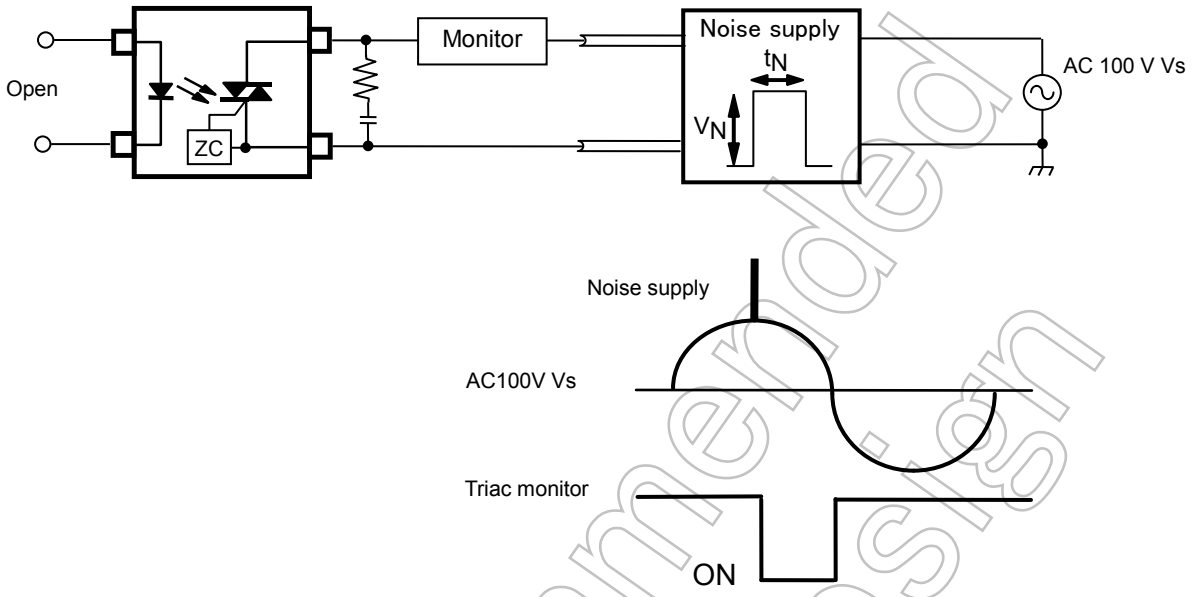
Note 3: impulse noise durability test circuit



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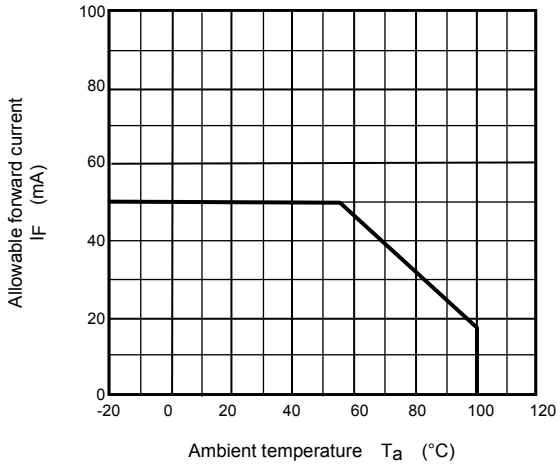
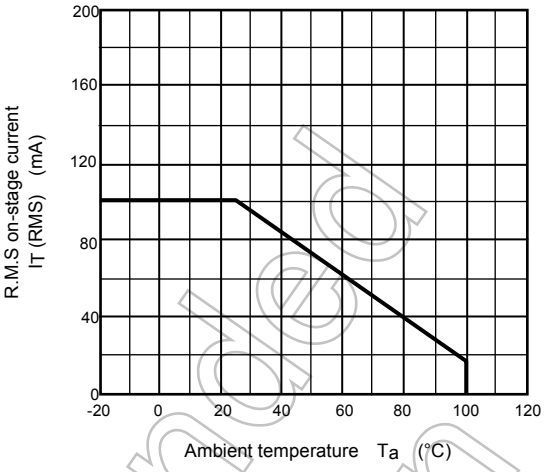
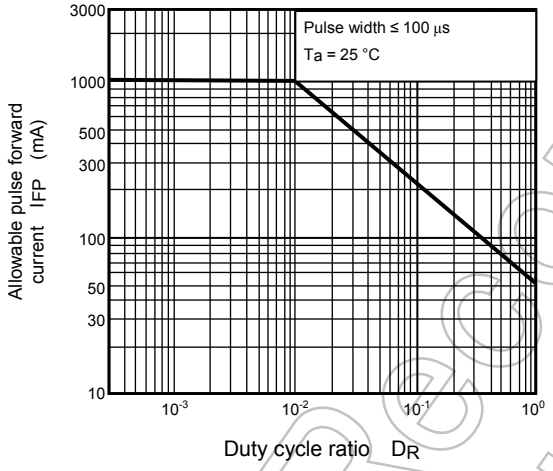
$I_F - T_a$



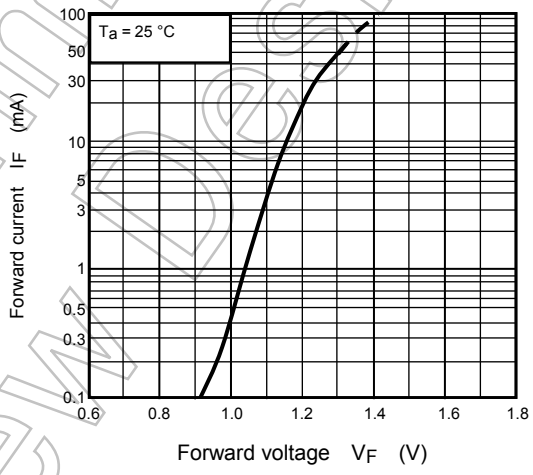
I_T (RMS) – T_a



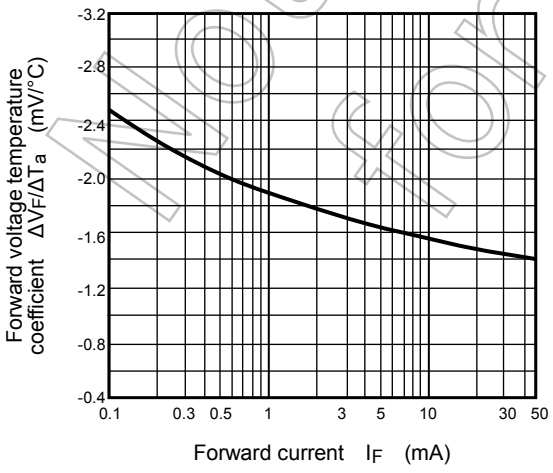
I_{FP} – D_R



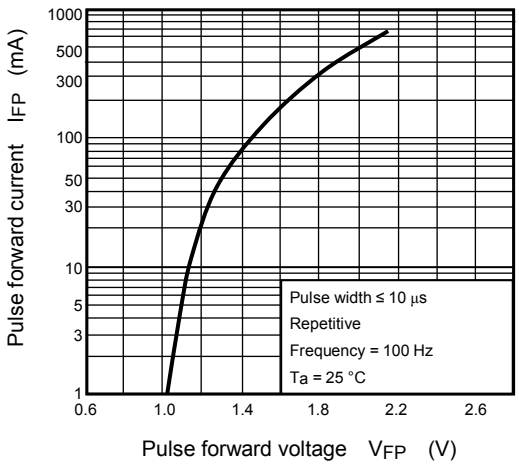
I_F – V_F



$\Delta V_F/\Delta T_a$ – I_F



I_{FP} – V_{FP}



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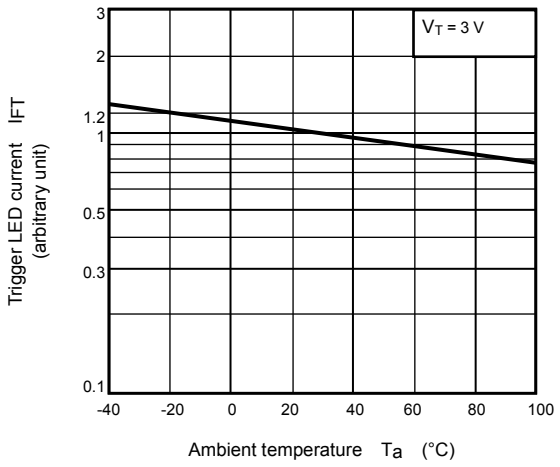
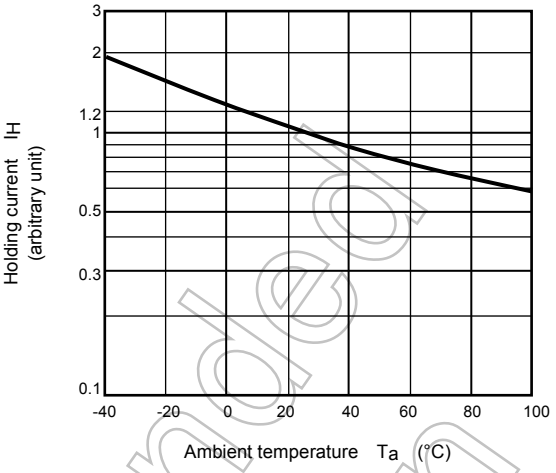
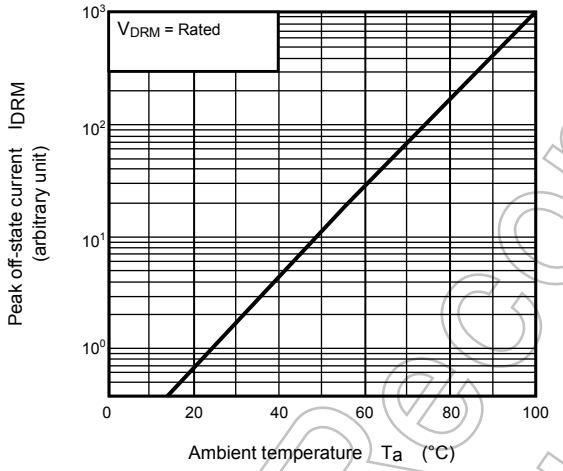
Normalized $I_{FT} - T_a$



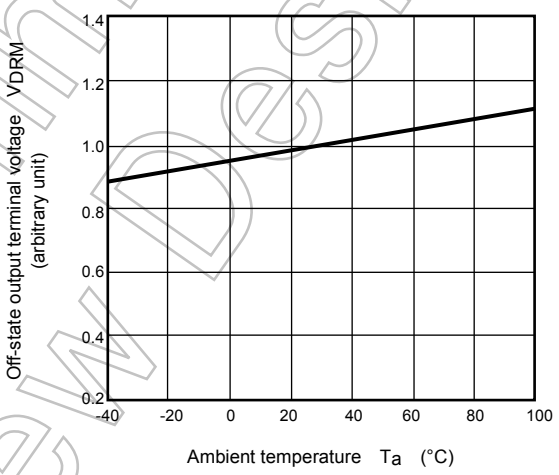
Normalized $I_H - T_a$



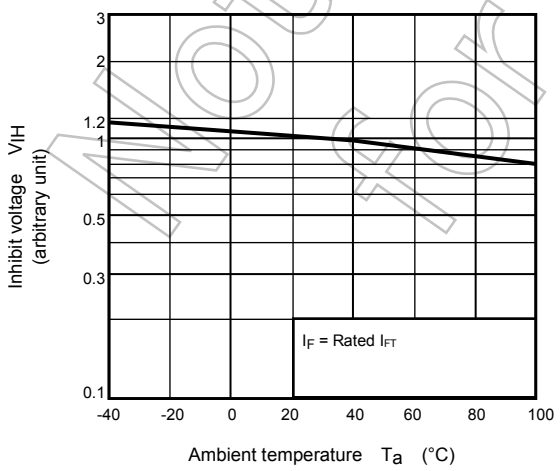
Normalized $I_{DRM} - T_a$



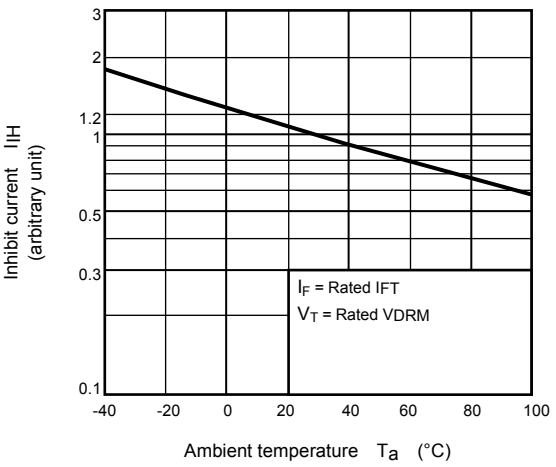
Normalized $V_{DRM} - T_a$



Normalized $V_{IH} - T_a$



Normalized $I_{IH} - T_a$



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